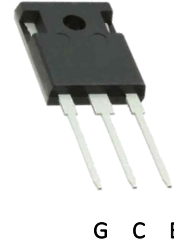


650V 75A CoolFAST™ 7 Technology IGBT

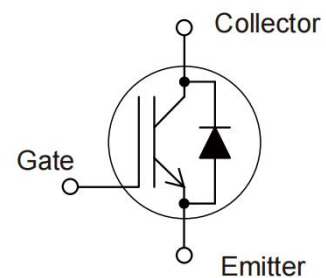
Features:

- Low Switching Power Loss
- Low Switching Surge and Noise
- Advanced Field Stop Technology
- Low EMI
- Maximum Junction Temperature 175°C
- Qualified According to JEDEC For Target Applications
- Pb-free Lead Plating, Halogen-free Mold Compound, RoHS Compliant



Applications:

- Industrial UPS
- Welding Machine
- Solar Converters
- Energy Storage
- EV Charger



Key Performance and Package Parameters

Type	V _{CE}	I _C	V _{CEsat} , T _{vj} =25°C	T _{vjmax}	Marking	Package
DKW75N65EX7	650V	75A	1.6 V	175°C	DKW75N65EX7	TO247-3

Maximum Ratings and Characteristics

Absolute Maximum Ratings at T_{vj}= 25°C (unless otherwise specified)

Items	Symbols	Value	Units
Collector-emitter voltage	V _{CES}	650	V
Gate-emitter voltage	V _{GES}	±20	V
Transient gate-emitter voltage (t _p ≤ 10μs, D < 0.010)		±30	
DC collector current, limited by T _{vjmax}	I _C	125	A
T _C = 25°C		75	
T _C = 100°C	I _{CP}	300	A
Pulsed collector current, t _p limited by T _{vjmax}	I _F	115	A
Diode forward current, limited by T _{vjmax}		75	
T _C = 25°C	I _{FP}	300	A
T _C = 100°C	T _{SC}	5	μs
Short circuit withstand time, V _{GE} = 15V, V _{CE} ≤ 400V	P _{D_IGBT}	500	W
IGBT max. power dissipation	P _{D_FWD}	454	W
FWD max. power dissipation	T _{vj}	-40 ~ +175	°C
Operating junction temperature	T _{stg}	-55 ~ +175	°C
Storage temperature			

Electrical Characteristics at $T_{vj}= 25^{\circ}\text{C}$ (unless otherwise specified)

Description	Symbols	Conditions	Characteristics			Unit
			Min	Typ	Max	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}= 0\text{V}, I_C= 0.50\text{mA}$	650	-	-	V
Zero gate voltage collector current	I_{CES}	$V_{CE}= 650\text{V}, V_{GE}= 0\text{V}$	-	-	200	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}= 0\text{V}, V_{GE}= \pm 20\text{V}$	-	-	± 200	nA
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE}= V_{GE}, I_C= 250\mu\text{A}$	5.0	5.8	6.6	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}= 15\text{V}, I_C= 75\text{A}$	-	1.6	2.25	V
		$T_{vj}= 25^{\circ}\text{C}$ $T_{vj}= 175^{\circ}\text{C}$	-	2.0	-	-
Input capacitance	C_{ies}	$V_{CE}= 25\text{V}, V_{GE}= 0\text{V}$ $f= 1\text{MHz}$	-	8385	-	pF
Output capacitance	C_{oes}		-	235	-	pF
Reverse transfer capacitance	C_{res}		-	62	-	pF
Gate charge	Q_G	$V_{CC}= 520\text{V}, I_C= 75\text{A}, V_{GE}= 15\text{V}$	-	333	-	nC
Forward voltage drop	V_F	$I_F= 75\text{A}$	-	1.55	3.0	V
		$T_{vj}= 25^{\circ}\text{C}$ $T_{vj}= 175^{\circ}\text{C}$	-	1.4	-	-

Switching Characteristics at $T_{vj}= 25^{\circ}\text{C}$

Description	Symbols	Conditions	Characteristics			Unit
			Min	Typ	Max	
IGBT Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{CC}= 400\text{V}$ $I_C= 75\text{A}$ $V_{GE}= 15\text{V}$ $R_G= 10\Omega$ Inductive load	-	79	-	ns
Rise time	t_r		-	146	-	ns
Turn-off delay time	$t_{d(off)}$		-	215	-	ns
Fall time	t_f		-	56	-	ns
Turn-on energy	E_{on}		-	4.5	-	mJ
Turn-off energy	E_{off}		-	1.7	-	mJ
Total switching energy	E_{ts}		-	6.2	-	mJ
Diode Characteristics						
Diode reverse recovery time	t_{rr}	$V_{CC}= 400\text{V}$	-	95	-	ns
Diode reverse recovery charge	Q_{rr}	$I_F= 75\text{A}$	-	1.0	-	μC
Diode peak reverse recovery current	I_{rrm}	$di_F/dt= 500\text{A}/\mu\text{s}$	-	18.3	-	A

Switching Characteristics at $T_{vj}= 175^{\circ}\text{C}$

Description	Symbols	Conditions	Characteristics			Unit
			Min	Typ	Max	
IGBT Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{CC}= 400\text{V}$ $I_C= 75\text{A}$ $V_{GE}= 15\text{V}$ $R_G= 10\Omega$ Inductive load	-	66	-	ns
Rise time	t_r		-	141	-	ns
Turn-off delay time	$t_{d(off)}$		-	237	-	ns
Fall time	t_f		-	63	-	ns
Turn-on energy	E_{on}		-	4.7	-	mJ
Turn-off energy	E_{off}		-	1.9	-	mJ
Total switching energy	E_{ts}		-	6.6	-	mJ
Diode Characteristics						
Diode reverse recovery time	t_{rr}	$V_{CC}= 400\text{V}$	-	240	-	ns
Diode reverse recovery charge	Q_{rr}	$I_F= 75\text{A}$	-	8.1	-	μC
Diode peak reverse recovery current	I_{rrm}	$di_F/dt= 500\text{A}/\mu\text{s}$	-	49.6	-	A

Thermal Resistance

Items	Symbols	Characteristics			Unit
		Min	Typ	Max	
Thermal resistance, junction-ambient	$R_{th(j-a)}$	-	-	50	°C /W
Thermal resistance, IGBT junction to case	$R_{th(j-c)}$	-	-	0.3	
Thermal resistance, diodes junction to case	$R_{th(j-c)}$	-	-	0.33	

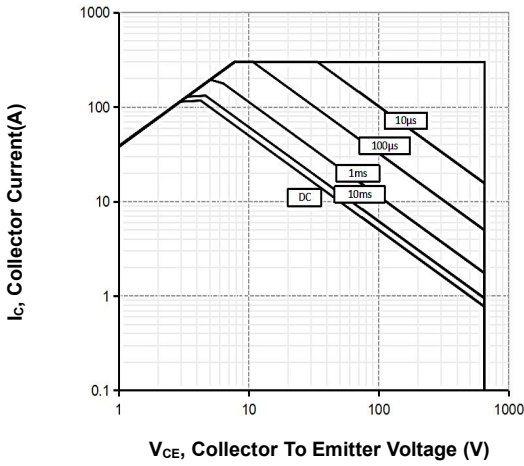


Figure 1. Forward bias safe operating area
($D = 0$, $T_c = 25^\circ\text{C}$, $T_{vj} \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$)

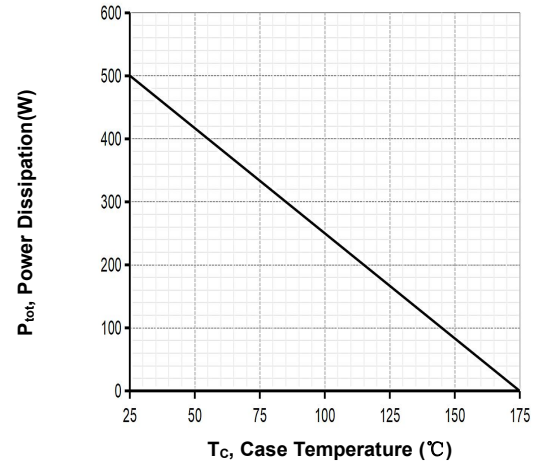


Figure 2. Power dissipation vs. case temperature
($T_{vj} \leq 175^\circ\text{C}$)

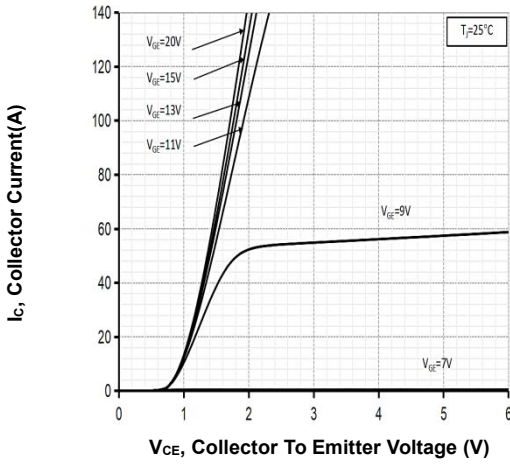


Figure 3. Typical output characteristic
($T_{vj} = 25^\circ\text{C}$)

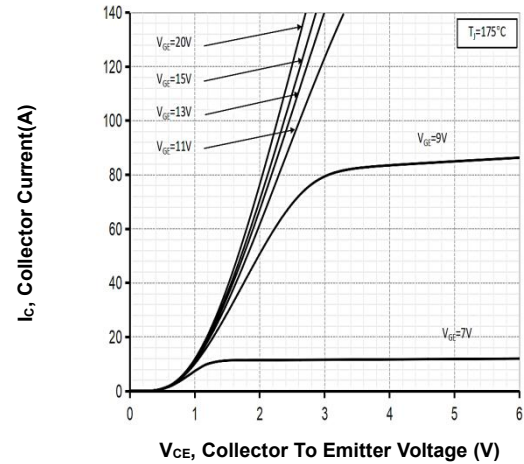


Figure 4. Typical output characteristic
($T_{vj} = 175^\circ\text{C}$)

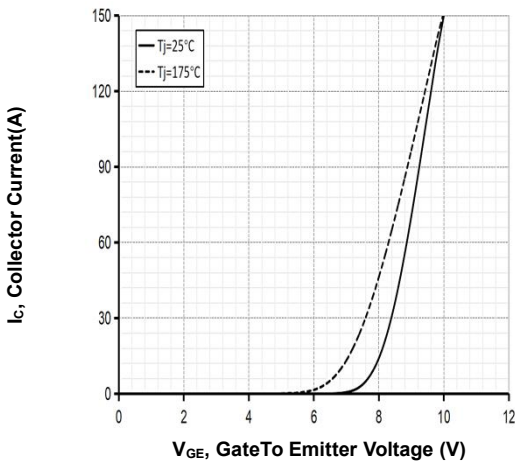


Figure 5. Typical transfer characteristic
($V_{CE} = 20\text{V}$)

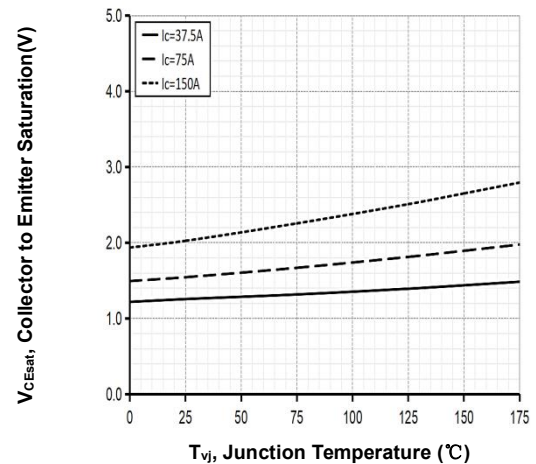


Figure 6. Typical collector-emitter saturation voltage vs. T_{vj} ($V_{GE} = 20\text{V}$)

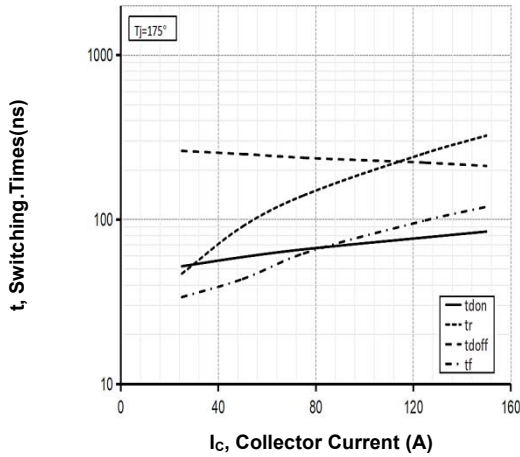


Figure 7. Typical switching times vs. collector current (Ind. load, $T_{vj} = 175^{\circ}\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 15/0\text{V}$, $R_G = 10\Omega$)

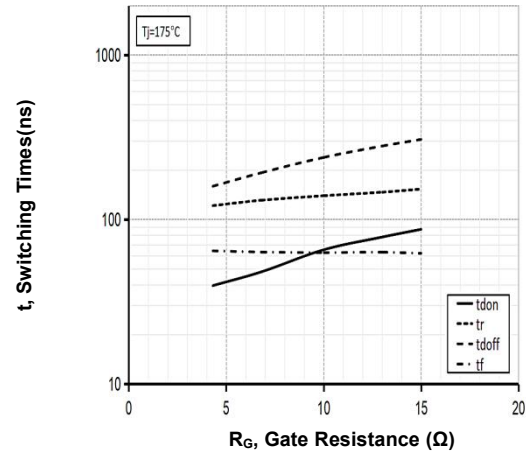


Figure 8. Typical switching times vs. gate resistor (Ind. Load, $T_{vj} = 175^{\circ}\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 15/0\text{V}$, $I_C = 75\text{A}$)

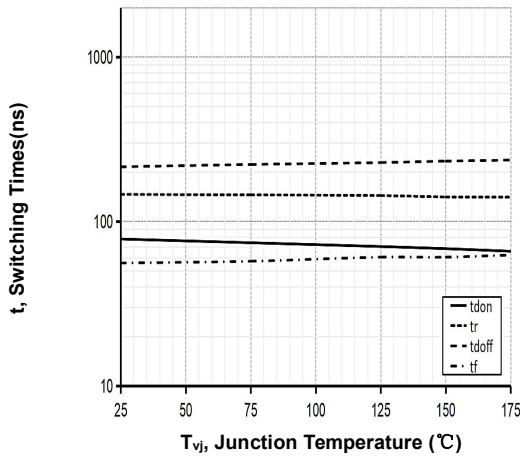


Figure 9. Typical switching times vs. T_{vj} (Ind. Load, $V_{CE} = 400\text{V}$, $V_{GE} = 15/0\text{V}$, $I_C = 75\text{A}$, $R_G = 10\Omega$)

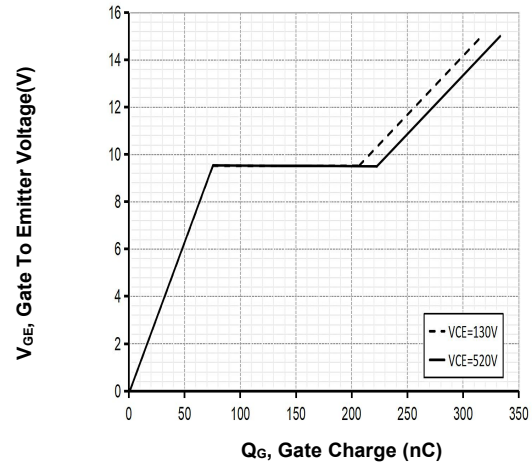


Figure 10. Typical gate charge ($I_C = 75\text{A}$)

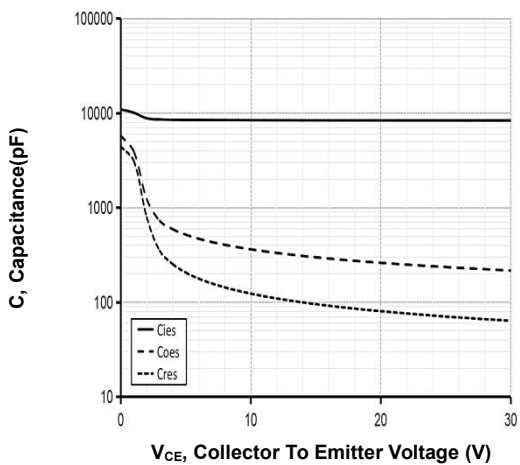


Figure 11. Typical capacitance vs. collector-emitter voltage ($V_{GE} = 0\text{V}$, $f = 1\text{MHz}$)

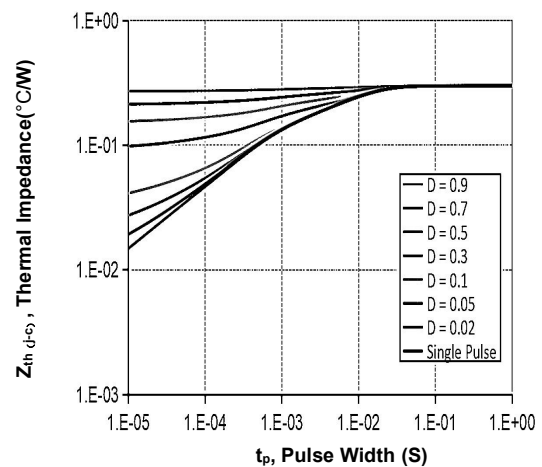


Figure 12. IGBT transient thermal impedance ($D = t_p/T$)

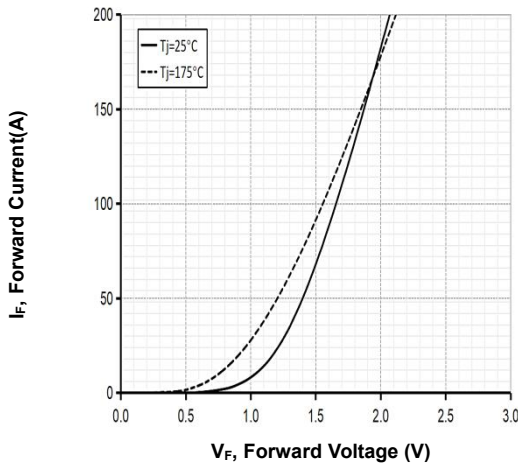


Figure 13. Typical diode forward current vs. forward voltage

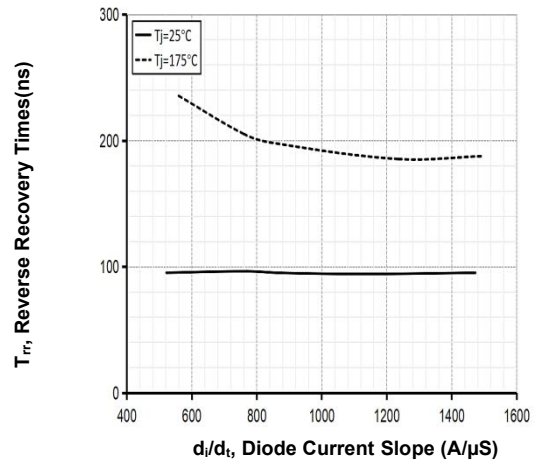


Figure 14. Typical reverse recovery time vs. diode current slope ($V_R = 400V$)

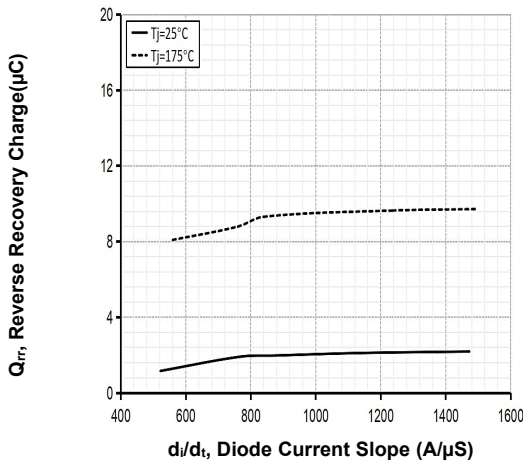


Figure 15. Typical reverse recovery charge vs. diode current slope ($V_R = 400V$)

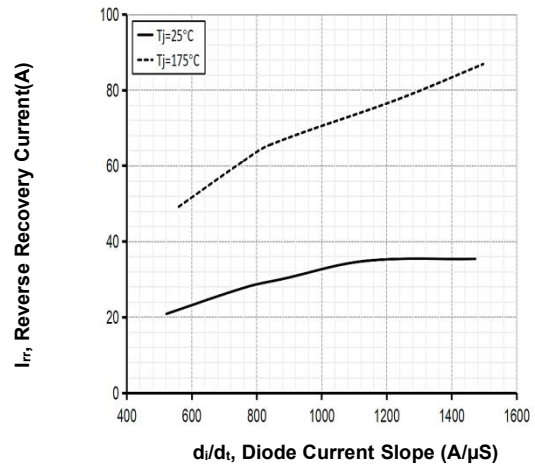
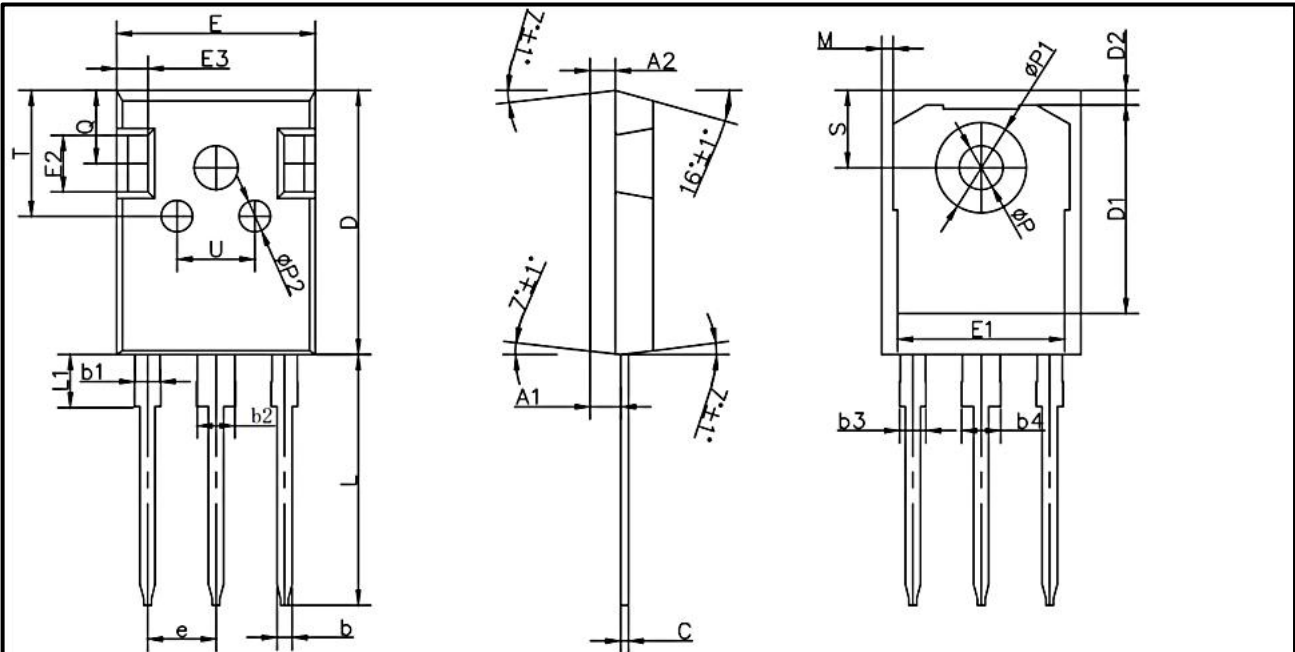


Figure 16. Typical reverse recovery current vs. diode current slope ($V_R = 400V$)

TO247-3 Package Outline



TO247-3L			
DIM.	MIN.	NOM.	MAX.
A	4.90	5.00	5.10
A1	2.25	2.36	2.51
A2	1.90	2.00	2.10
b	1.16	1.20	1.26
b1	1.96	2.00	2.06
b2	2.96	3.00	3.06
b3	-	-	2.25
b4	-	-	3.25
c	0.59	0.60	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.26	13.50
E2	4.40	4.50	4.60
E3	2.40	2.50	2.60
e	5.436BSC		
L	19.80	19.90	20.10
L1	-	-	4.30
M	0.35	0.89	0.95
P	3.40	3.50	3.60
P1	7.00	7.20	7.40
P2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40

All dimensions in millimeters

Revision History

Revision	Date	Subjects (major changes since last revision)
0.1	2021-03-20	Target version
1.1	2022-11-11	Preliminary version
1.2	2023-05-18	Sample version
1.3	2024-2-5	MP version

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